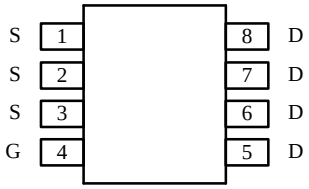
P-Channel Enhancement-Mode MOSFET

Product Summary

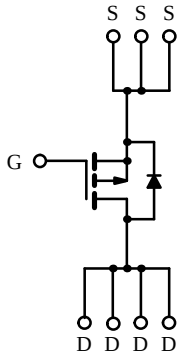
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
–20	0.045 @ V_{GS} = –4.5 V	± 5.4
	0.070 @ V_{GS} = –2.7 V	± 4.2

Recommended upgrade: Si9424DY
Lower profile/smaller size see: Si6433DQ

SO-8



Top View



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	–20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	± 5.4	A
	T_A = 70°C		± 4.4	
Pulsed Drain Current		I_{DM}	± 20	
Continuous Source Current (Diode Conduction)[a]		I_S	–2.6	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient[a]	R_{thJA}	50	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70125 .

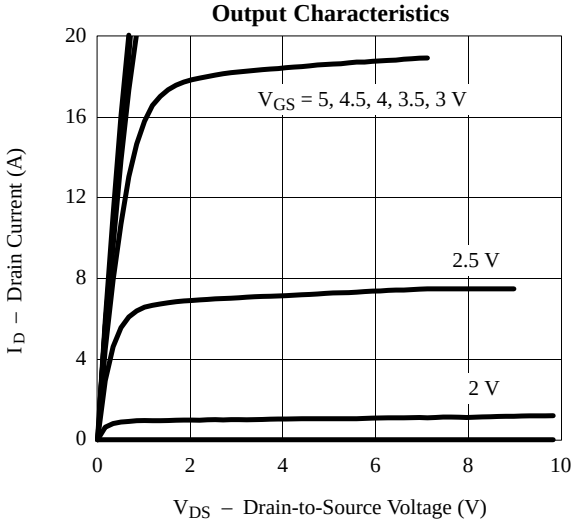
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 µA	–0.8			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –16 V, V_{GS} = 0 V			–1	µA
		V_{DS} = –10 V, V_{GS} = 0 V, T_J = 70°C			–5	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} ≤ –5 V, V_{GS} = –4.5 V	–20			A
		V_{DS} ≤ –5 V, V_{GS} = –2.7 V	–5			
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = –4.5 V, I_D = –5.1 A		0.032	0.045	Ω
		V_{GS} = –2.7 V, I_D = –2.0 A		0.052	0.070	
Forward Transconductance[b]	g_{fs}	V_{DS} = –9 V, I_D = –5.1 A		15		S
Diode Forward Voltage[b]	V_{SD}	I_S = –2.6 A, V_{GS} = 0 V		–0.76	–1.2	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = –6 V, V_{GS} = –4.5 V, I_D = –5.1 A		20	60	nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			7		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = –6 V, R_L = 6 Ω I_D ≅ –1 A, V_{GEN} = –4.5 V, R_G = 6 Ω		34	60	ns
Rise Time	t_r			70	100	
Turn-Off Delay Time	$t_{d(off)}$			76	180	
Fall Time	t_f			61	100	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = –2.6, di/dt = 100 A/µs		60	80	

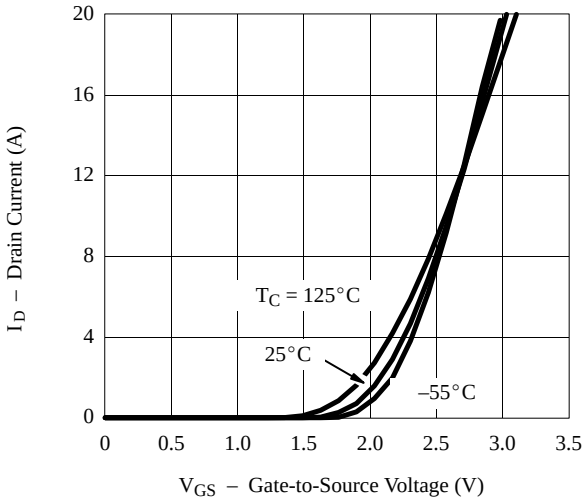
Notes
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.

Typical Characteristics (25°C Unless Otherwise Noted)

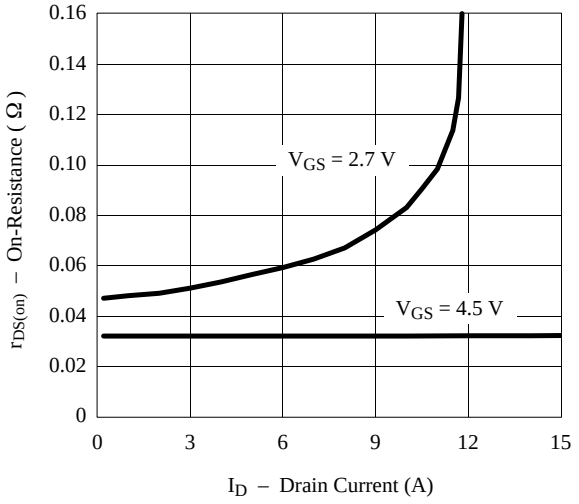
Output Characteristics



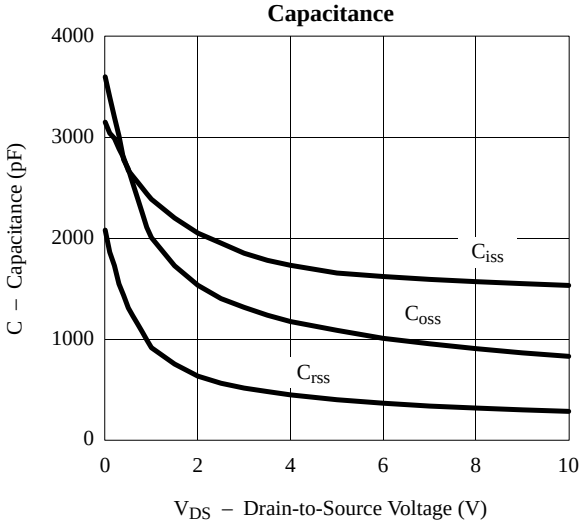
Transfer Characteristics



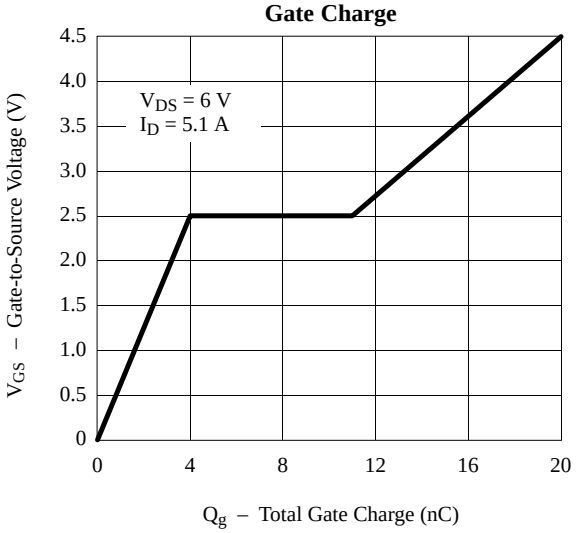
On-Resistance vs. Drain Current



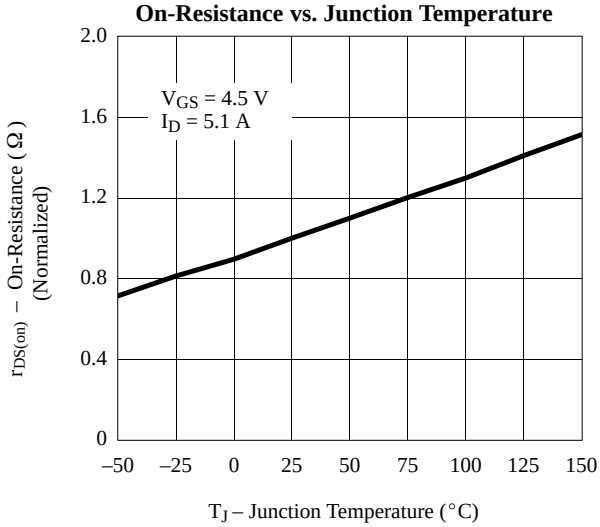
Capacitance



Gate Charge

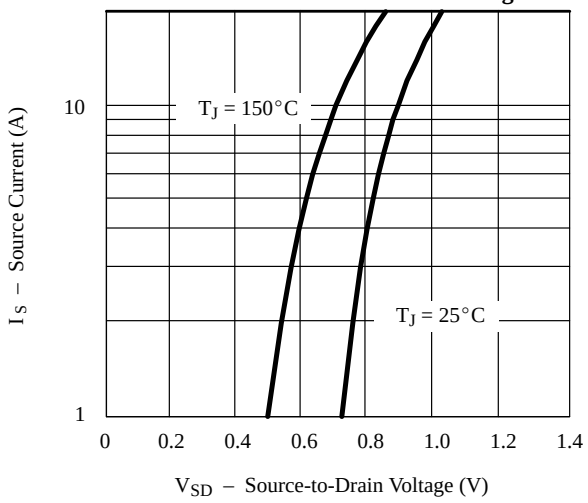


On-Resistance vs. Junction Temperature

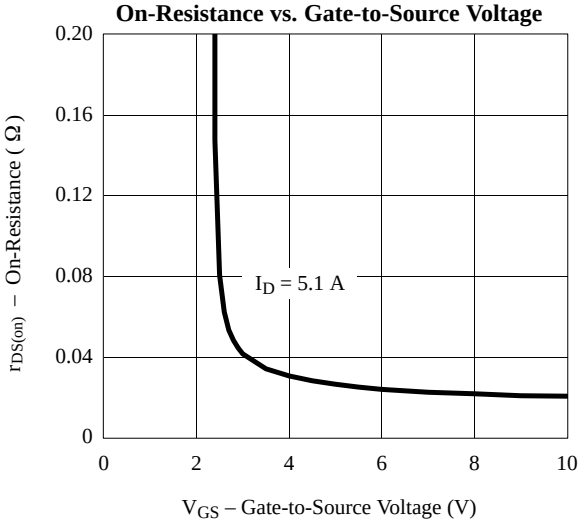


Typical Characteristics (25°C Unless Otherwise Noted)

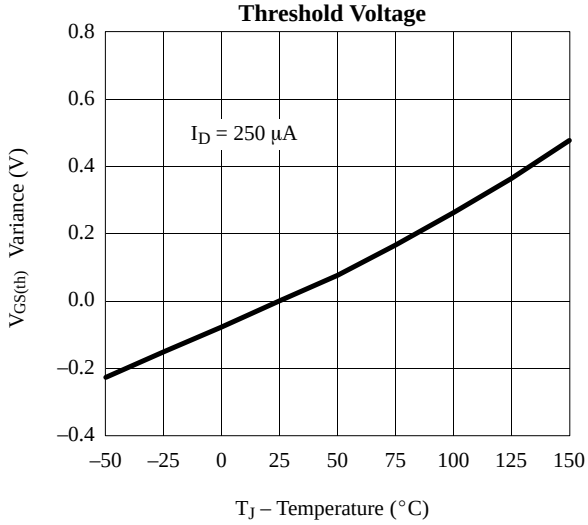
Source-Drain Diode Forward Voltage



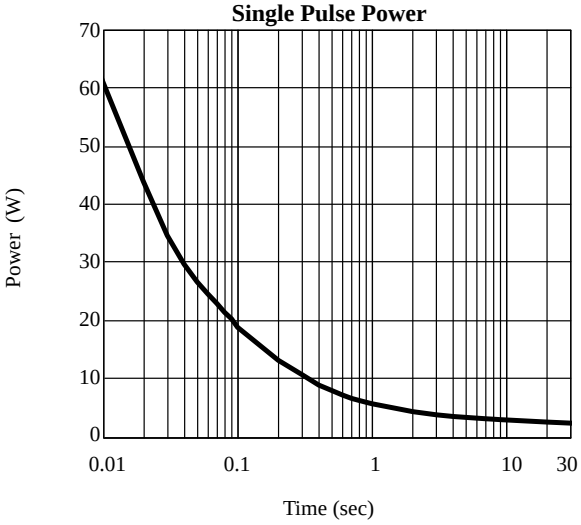
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient